

# N-channel 30 V 6.5 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 24 October 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	71	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	58	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	6.9	8.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	5.5	6.5	mΩ
Dynamic cl	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 15 \text{ V};$ see Figure 14; see Figure 15	-	2.6	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 15 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9	-	nC



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	-  q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R0-30YLB	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	71	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	50	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4	-	283	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	58	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	210	-	V
Source-dra	ain diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	53	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$	-	283	А
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 71 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped; see Figure 3	-	13	mJ

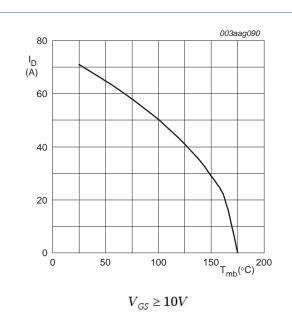


Fig 1. Continuous drain current as a function of mounting base temperature

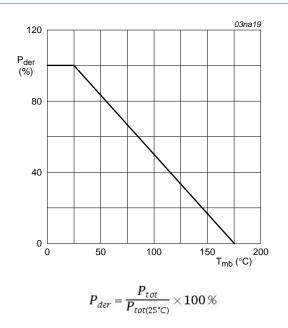
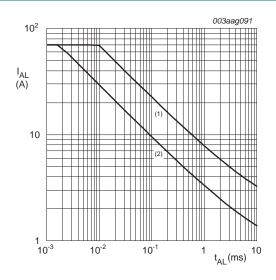


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1)  $T_{j (init)} = 25^{\circ}C$ ; (2)  $T_{j (init)} = 100^{\circ}C$ 

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

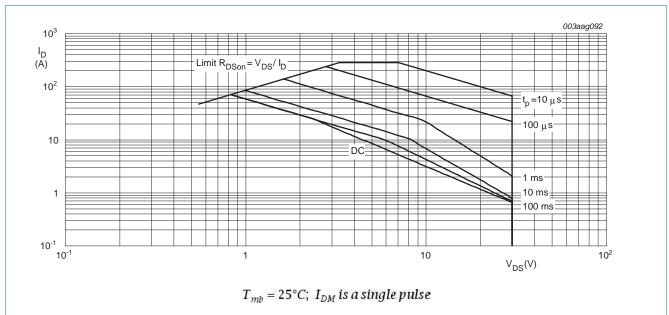
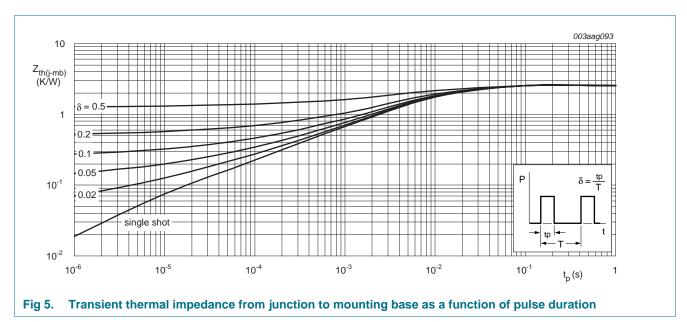


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.35	2.57	K/W



## 6. Characteristics

Table 6. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.48	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V; } I_D = 20 \text{ A; } T_j = 25 \text{ °C; see}$ Figure 12	-	6.9	8.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	5.5	6.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	10.7	mΩ
$R_G$	gate resistance	f = 1 MHz	-	1.62	3.24	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	19	-	nC	
		$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15	-	17	-	nC
$Q_{GS}$	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	0.6	-	nC
$Q_{GD}$	gate-drain charge		-	2.6	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.39	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1088	-	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	278	-	pF
Crss	reverse transfer capacitance		-	78	-	pF
d(on)	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	16	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	15	-	ns
d(off)	turn-off delay time		-	29	-	ns

PSMN6R0-30YLB

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 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	7.2	-	nC
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.85	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	25.5	-	ns
$Q_r$	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	15	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$	-	15.9	-	ns
t <sub>b</sub>	reverse recovery fall time	$dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{DS} = 15 \text{ V}$ ; see Figure 18	-	9.6	-	ns

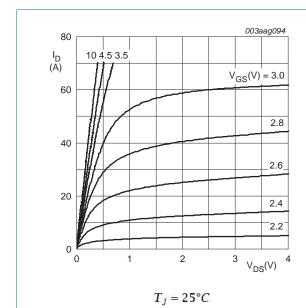
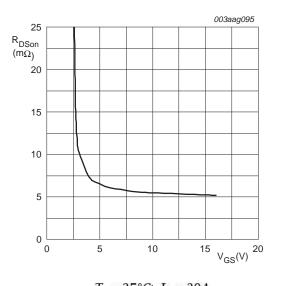


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

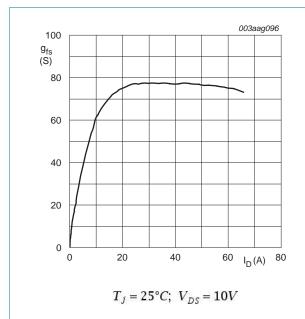


Fig 8. Forward transconductance as a function of drain current; typical values

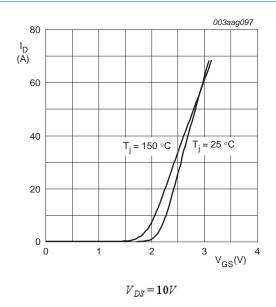


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

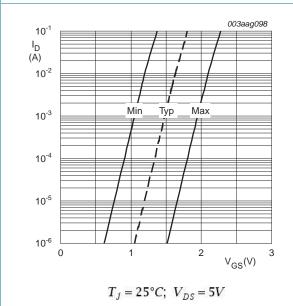


Fig 10. Sub-threshold drain current as a function of gate-source voltage

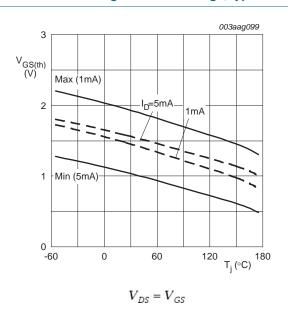


Fig 11. Gate-source threshold voltage as a function of junction temperature

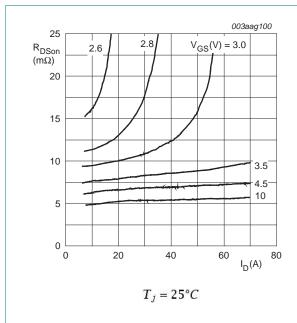


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

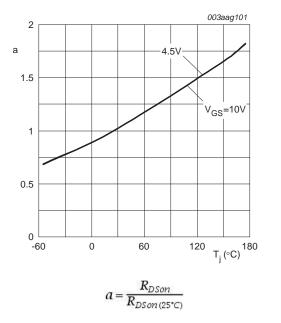


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

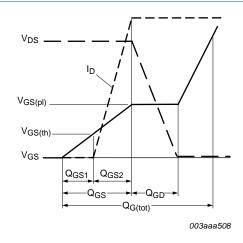
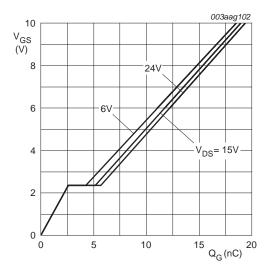


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

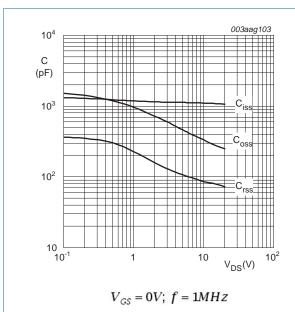


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

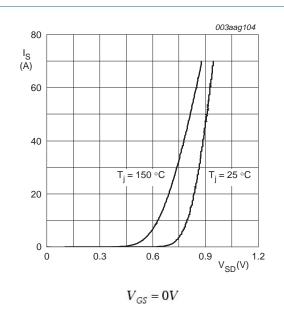


Fig 17. Source current as a function of source-drain voltage; typical values

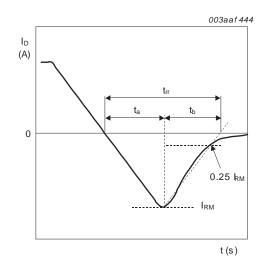
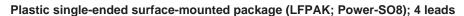
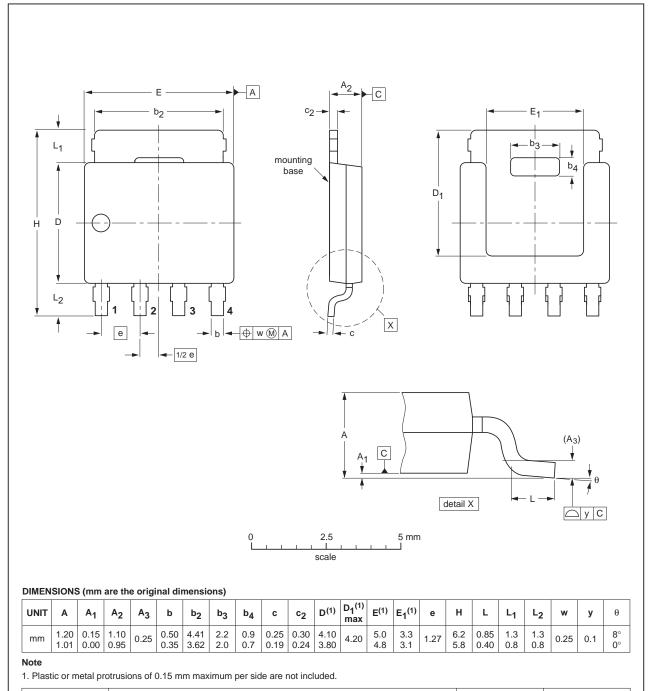


Fig 18. Reverse recovery timing definition

## 7. Package outline



**SOT669** 



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT669		MO-235			<del>06-03-16</del> 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YLB v.2	20111024	Product data sheet	-	PSMN6R0-30YLB v.1
Modifications:	<ul> <li>Status changed fro</li> </ul>	m preliminary to product.		
	<ul> <li>Various changes to</li> </ul>	content.		
PSMN6R0-30YLB v.1	20110908	Preliminary data sheet	-	-

### N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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## **Nexperia**

## PSMN6R0-30YLB

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- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



**«JONHON»** (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«**FORSTAR**» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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